Si-based electronics The last ITRS node... Is there life beyond it?

W. Kuzmicz Warsaw University of Technology

> First NANO-TEC Workshop Granada, 20 January 2011

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Let's look for it and call it a bridge technology

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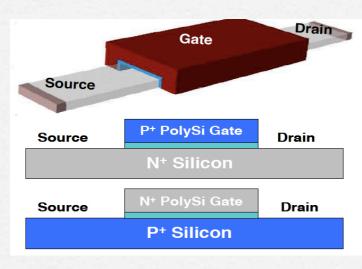
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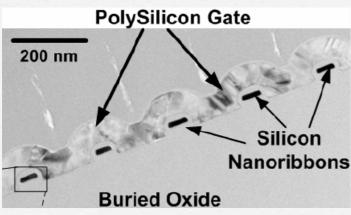


Junctionless FET

SOI Gated Resistor

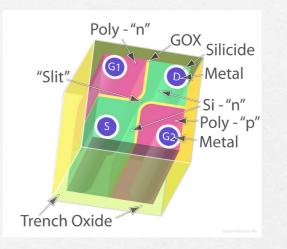
J.P.Colinge et al., 2009 IEEE Int. SOI Conf.

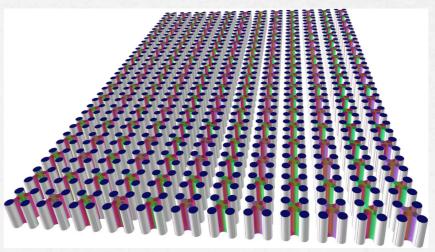




Vertical Slit FET

W. Maly, US patent application 2007





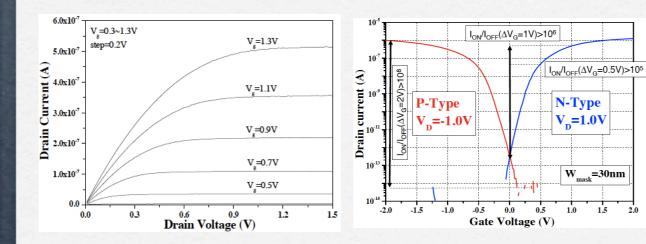
Source: J.P.Colinge et al., conference presentation

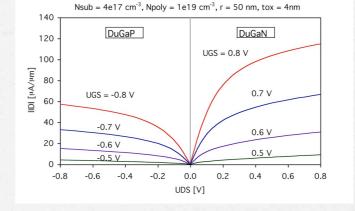
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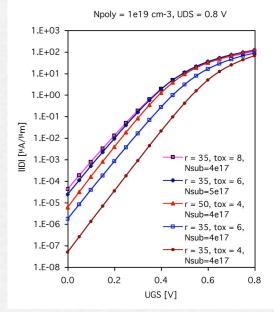
Ideal subthreshold characteristics: ~60 mV/decade, good output characteristics





Source: J.P.Colinge et al., conference presentation

Source: courtesy of A. Pfitzner, Warsaw Univ. of Technology



Experimentally confirmed

1.5

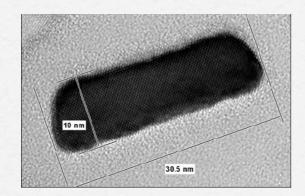
2.0



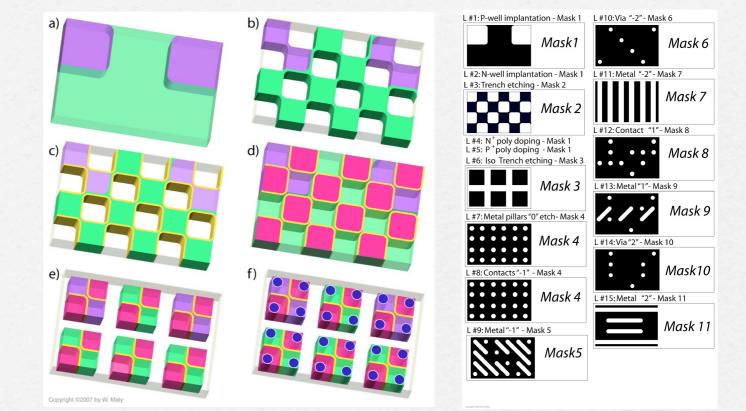
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Technology: Si nanoribbon on SOI



VESTIC technology: All processes routinely used in CMOS, litho friendly

Source: J.P.Colinge et al., conference presentation

Source: courtesy of W. Maly

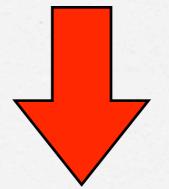
Benchmarking

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We don't need individual devices, we need circuits and systems

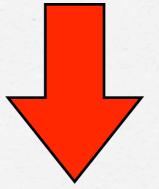
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What should be assessed is the <u>circuit performance</u>, not raw device characteristics

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- 6. <u>Cost per function (...but can we estimate it?)</u>

Tech	Version	Performance	Integrability	Manufactura bility	Variability and yield	Design	Cost(?)
Fin FET							
	•••						
TFET							
Jless FET							
	•••						

Thank you!

Now it's YOUR turn: questions and suggestions, please!